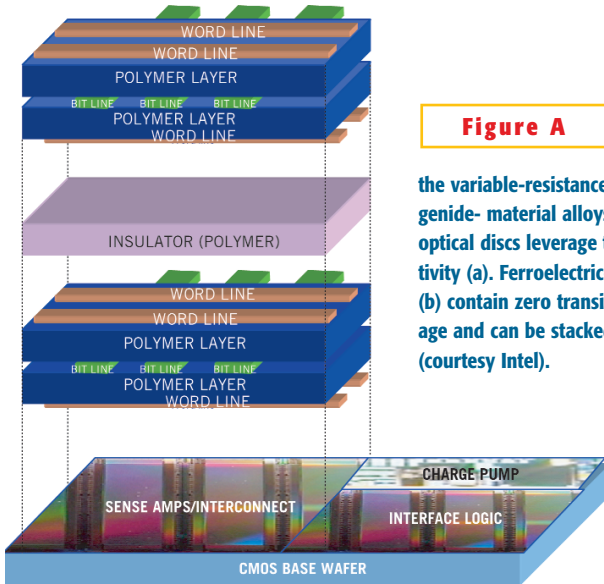


(a)



(b)

Figure A Phase-change memory employs the variable-resistance attributes of chalcogenide-material alloys, whereas writable optical discs leverage their variable reflectivity (a). Ferroelectric-polymer memories (b) contain zero transistors per bit of storage and can be stacked in three dimensions (courtesy Intel).

